

DESCRIPTION

The RH137 negative adjustable regulator will deliver up to 1.5A output current over an output voltage range of $-1.2V$ to $-22V$.

Every effort has been made to make these devices easy to use and difficult to damage. Internal current and power limiting coupled with true thermal limiting prevents device damage due to overloads or shorts, even if the regulator is not fastened to a heat sink.

Maximum reliability is attained with Linear Technology's advanced processing techniques combined with a 100% burn-in in the thermal limit mode. This assures that all device protection circuits are working and eliminates field failures experienced with other regulators that receive only standard electrical testing.

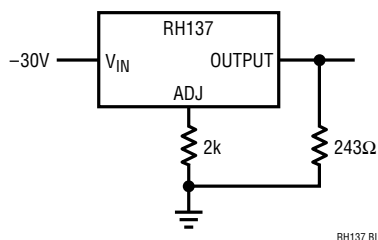
The wafer lots are processed to Linear Technology's in-house Class S flow to yield circuits usable in stringent military applications.

ABSOLUTE MAXIMUM RATINGS

Power Dissipation	Internally Limited
Input-to-Output Voltage Differential	30V
Operating Junction Temperature Range	$-55^{\circ}C$ to $150^{\circ}C$
Storage Temperature Range	$-65^{\circ}C$ to $150^{\circ}C$
Lead Temperature (Soldering, 10 sec)	$300^{\circ}C$

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BURN-IN CIRCUIT



PACKAGE/ORDER INFORMATION

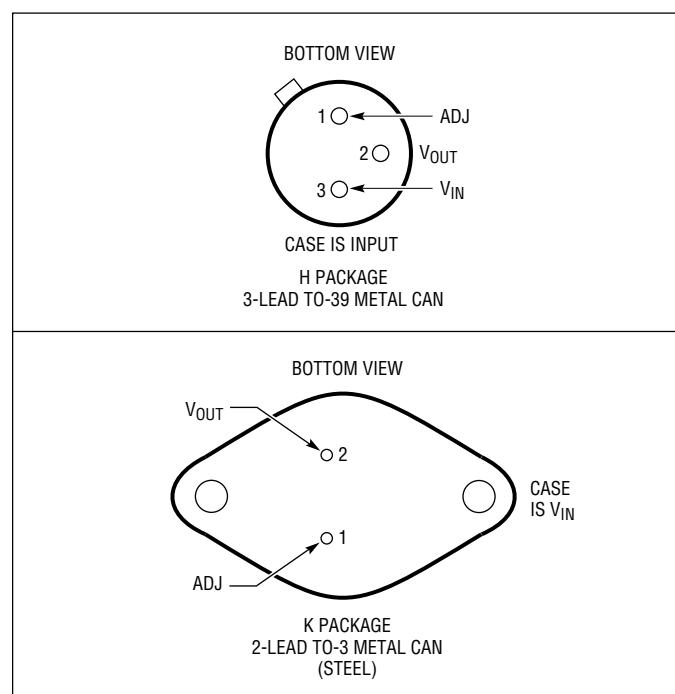


TABLE 1: ELECTRICAL CHARACTERISTICS (Preirradiation) (Note 1)

SYMBOL	PARAMETER	CONDITIONS	NOTES	$T_A = 25^\circ\text{C}$			SUB-GROUP	$-55^\circ\text{C} \leq T_A \leq 150^\circ\text{C}$			SUB-GROUP	UNITS
				MIN	TYP	MAX		MIN	TYP	MAX		
V_{REF}	Reference Voltage	$ V_{IN} - V_{OUT} = 5\text{V}, I_{OUT} = 10\text{mA}$		-1.225	-1.275		1					V
		$3\text{V} \leq V_{IN} - V_{OUT} \leq 30\text{V},$ $10\text{mA} \leq I_{OUT} \leq I_{MAX}, P \leq P_{MAX}$		-1.200	-1.300		1	-1.200	-1.300	2, 3		V
$\frac{\Delta V_{OUT}}{\Delta V_{IN}}$	Line Regulation	$3\text{V} \leq V_{IN} - V_{OUT} \leq 30\text{V}$	2		0.02		1		0.05	2, 3	%/V	
$\frac{\Delta V_{OUT}}{\Delta I_{OUT}}$	Load Regulation	$10\text{mA} \leq I_{OUT} \leq I_{MAX}, V_{OUT} \leq 5\text{V}$	2		25		1		50	2, 3	mV	
		$10\text{mA} \leq I_{OUT} \leq I_{MAX}, V_{OUT} \geq 5\text{V}$	2		0.5		1		1	2, 3	%	
	Thermal Regulation	10ms Pulse			0.02		1				%/W	
	Ripple Rejection	$V_{OUT} = -10\text{V}, f = 120\text{Hz}, C_{ADJ} = 0$			60						dB	
		$V_{OUT} = -10\text{V}, f = 120\text{Hz},$ $C_{ADJ} = 10\mu\text{F}$	3	66				66			dB	
I_{ADJ}	Adjust Pin Current				100		1		100	2, 3	μA	
ΔI_{ADJ}	Adjust Pin Current Change	$10\text{mA} \leq I_{OUT} \leq I_{MAX}$			5		1		5	2, 3	μA	
		$3\text{V} \leq V_{IN} - V_{OUT} \leq 30\text{V}$			5		1		5	2, 3	μA	
I_{MIN}	Minimum Load Current	$ V_{IN} - V_{OUT} = 30\text{V}$			5		1		5	2, 3	mA	
		$ V_{IN} - V_{OUT} \leq 10\text{V}$			3		1		3	2, 3	mA	
	Current Limit	$ V_{IN} - V_{OUT} \leq 15\text{V}$	H Package	5	0.5		1	0.5		2, 3	A	
			K Package	5	1.5		1	1.5		2, 3	A	
		$ V_{IN} - V_{OUT} = 30\text{V}$	H Package	5	0.15		1				A	
			K Package	5	0.24		1				A	
$\frac{\Delta V_{OUT}}{\Delta \text{Temp}}$	Temperature Stability	$-55^\circ\text{C} \leq T_J \leq 125^\circ\text{C}$	3					0.6			%	
$\frac{\Delta V_{OUT}}{\Delta \text{Time}}$	Long Term Stability	$T_A = 125^\circ\text{C}$	3						1		%	
e_n	RMS Output Noise	$10\text{Hz} \leq f \leq 10\text{kHz}$			0.003						%	
θ_{JC}	Thermal Resistance (Junction to Case)	H Package	3		15						$^\circ\text{C}/\text{W}$	
		K Package	3		3						$^\circ\text{C}/\text{W}$	

TABLE 1A: ELECTRICAL CHARACTERISTICS (Postirradiation) (Note 4)

SYMBOL	PARAMETER	CONDITIONS	NOTES	10KRAD(Si)		20KRAD(Si)		50KRAD(Si)		100KRAD(Si)		200KRAD(Si)		UNITS
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
V_{REF}	Reference Voltage	$ V_{IN} - V_{OUT} \leq 5\text{V},$ $I_{OUT} = 10\text{mA}$		-1.225	-1.275	-1.225	-1.275	-1.225	-1.275	-1.225	-1.275	-1.22	-1.28	V
		$3\text{V} \leq V_{IN} - V_{OUT} \leq 30\text{V},$ $10\text{mA} \leq I_{OUT} \leq I_{MAX}, P \leq P_{MAX}$		-1.2	-1.3	-1.2	-1.3	-1.2	-1.3	-1.2	-1.3	-1.2	-1.3	V
$\frac{\Delta V_{OUT}}{\Delta V_{IN}}$	Line Regulation	$3\text{V} \leq V_{IN} - V_{OUT} \leq 30\text{V},$	2		0.02		0.02		0.02		0.02		0.02	%/V
$\frac{\Delta V_{OUT}}{\Delta I_{OUT}}$	Load Regulation	$10\text{mA} \leq I_{OUT} \leq I_{MAX},$ $ V_{OUT} \leq 5\text{V}$	2		25		25		25		25		25	mV
		$10\text{mA} \leq I_{OUT} \leq I_{MAX},$ $ V_{OUT} \geq 5\text{V}$	2		0.5		0.5		0.5		0.5		0.5	%

TABLE 1A: ELECTRICAL CHARACTERISTICS (Postirradiation) (Note 4)

SYMBOL	PARAMETER	CONDITIONS	NOTES	10KRAD(Si)		20KRAD(Si)		50KRAD(Si)		100KRAD(Si)		200KRAD(Si)		UNITS
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
I_{ADJ}	Adjust Pin Current				100		100		100		100		100	μA
ΔI_{ADJ}	Adjust Pin Current Change	$10\text{mA} \leq I_{OUT} \leq I_{MAX}$ $3\text{V} \leq V_{IN} - V_{OUT} \leq 30\text{V}$			5		5		5		5		5	μA
I_{MIN}	Minimum Load Current	$ V_{IN} - V_{OUT} = 30\text{V}$ $ V_{IN} - V_{OUT} \leq 10\text{V}$			5		5		5		5		5	mA
					3		3		3		3		3	mA
	Current Limit	$ V_{IN} - V_{OUT} \leq 15\text{V}$ $ V_{IN} - V_{OUT} = 30\text{V}$			0.5		0.5		0.5		0.5		0.5	A
					0.15		0.15		0.15		0.15		0.15	A
	K Package	$ V_{IN} - V_{OUT} \leq 15\text{V}$ $ V_{IN} - V_{OUT} = 30\text{V}$			1.5		1.5		1.5		1.5		1.5	A
					0.24		0.24		0.24		0.24		0.24	A

Note 1: Unless otherwise specified, these specifications apply for $|V_{IN} - V_{OUT}| = 5\text{V}$; and $I_{OUT} = 0.1\text{A}$ for the H package (TO-39) and $I_{OUT} = 0.5\text{A}$ for the K package (TO-3) package. Although power dissipation is internally limited, these specifications are applicable for power dissipations of 2W for the TO-39 and 20W for the TO-3. I_{MAX} is 0.2A for the TO-39 and 1.5A for the TO-3 package.

Note 2: Regulation is measured at a constant junction temperature using pulse testing with a low duty cycle. Changes in output voltage due to heating effects are covered under the specification for thermal regulation.

Note 3: Guaranteed by design, characterization or correlation to other tested parameters.

Note 4: $T_J = 25^\circ\text{C}$ unless otherwise noted.

Note 5: I_{SC} is tested at the ambient temperatures of 25°C and -55°C . I_{SC} cannot be tested at the maximum ambient temperature of 150°C due to the high power level required. I_{SC} specification at 150°C ambient is guaranteed by characterization and correlation to 25°C testing.

TABLE 2: ELECTRICAL TEST REQUIREMENTS

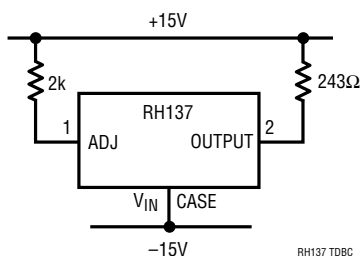
MIL-STD-883 TEST REQUIREMENTS	SUBGROUP
Final Electrical Test Requirements (Method 5004)	1*,2,3
Group A Test Requirements (Method 5005)	1,2,3
Group B and D End Point Electrical Parameters (Method 5005)	1,2,3

* PDA Applies to subgroup 1. See PDA Test Notes.

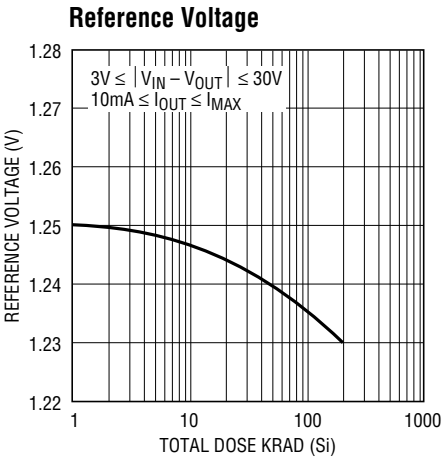
PDA Test Notes

The PDA is specified as 5% based on failures from group A, subgroup 1, tests after cooldown as the final electrical test in accordance with method 5004 of MIL-STD-883. The verified failures of group A, subgroup 1, after burn-in divided by the total number of devices submitted for burn-in in that lot shall be used to determine the percent for the lot.

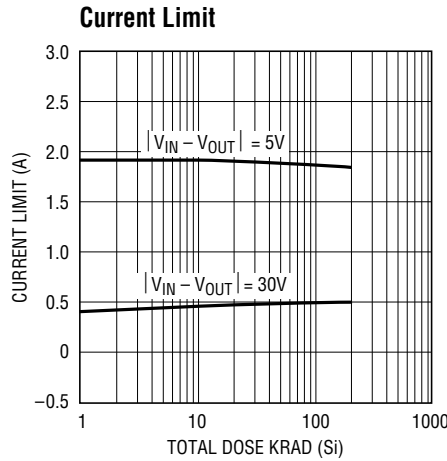
Linear Technology Corporation reserves the right to test to tighter limits than those given.

TOTAL DOSE BIAS CIRCUIT

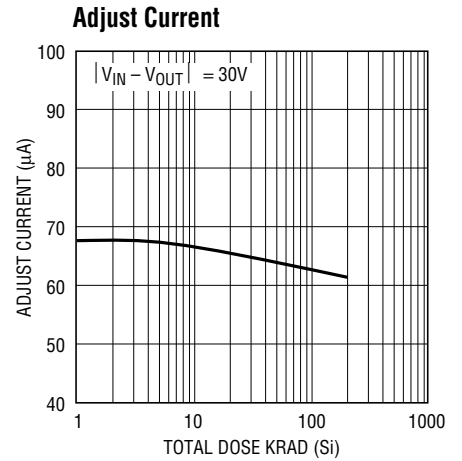
TYPICAL PERFORMANCE CHARACTERISTICS



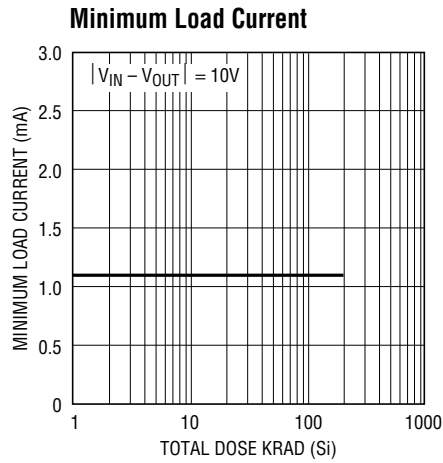
RH137 G01



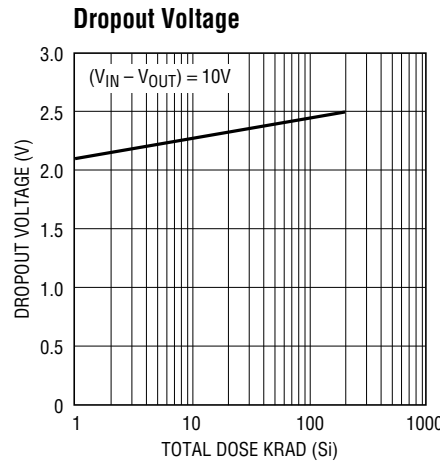
RH137 G02



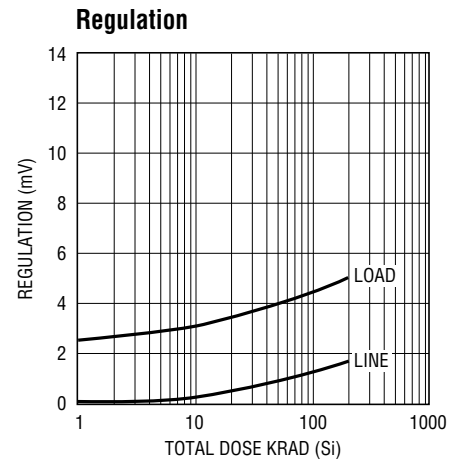
RH137 G03



RH137 G04



RH137 G05



RH137 G06